WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:

a first active fin protruding from a substrate;

a second active fin protruding from the substrate;

a first gate pattern crossing over both the first active fin and the second active fin~~covering a side surface and a top surface of the first active fin; and~~

a first source/drain pattern of a first conductivity on the first active fin;~~s at opposite sides of the first gate pattern, each of the first source/drain patterns including:~~

a second source/drain pattern of a second conductivity on the second active fin, the second conductivity being opposite to the first conductivity; and

a contact plug in direct contact with both the first source/drain pattern of the first conductivity and the second source/drain pattern of the second conductivity, an entire bottom surface of the contact plug being flat,

wherein the first source/drain pattern includes:

a first lower side and a second lower side spaced apart from each other,

a first upper side extended from the first lower side, and

a second upper side extended from the second lower side,

wherein the second source/drain pattern includes:

a third lower side and a fourth lower side spaced apart from each other,

a third upper side extended from a top end of the third lower side, and

a fourth upper side extended from the fourth lower side,

wherein the first lower side is inclined at a first angle relative to a top surface of the substrate, the second upper side is inclined at a second angle relative to the top surface of the substrate,

wherein the third lower side is inclined at a third angle relative to a straight line connecting a bottom end of the third lower side to a bottom end of the fourth lower side, and the first angle is greater than the second angle and the third angle,

wherein top surfaces of the first and second source/drain patterns are coplanar with each other, the top surfaces of the first and second source/drain patterns being in direct contact with the bottom surface of the contact plug.

2. The semiconductor device as claimed in claim 1, wherein the first angle ranges from about 55° to about 65°.

3. The semiconductor device as claimed in claim 1 or claim 2, further comprising:

a first point where the first lower side and the first upper side meet or an extension line of the first lower side and an extension line of the first upper side meet;

a second point where the second lower side and the second upper side meet or an extension line of the second lower side and an extension line of the second upper side meet;

a first segment connecting the first and second points to each other;

a third point where the first upper side and the second upper side meet or an extension line of the first upper side and an extension line of the second upper side meet;

a fourth point where an extension line of the first lower side and an extension line of the second lower side meet;

a second segment connecting the third point to the fourth point; and

a fifth point where the first segment and the second segment intersect, the fifth point being higher than a center point of the second segment.

4. The semiconductor device as claimed in claim 3, wherein a first distance from the third point to the fifth point is about 0.2 times to about 0.45 times a length of the second segment.

5. The semiconductor device as claimed in claim 1 or claim 2, further comprising:

~~a contact plug on the first source/drain pattern to be in contact with both of the first upper side and the second upper side;~~

a first contact point where the contact plug and the first upper side meet;

a second contact point where the contact plug and the second upper side meet;

a first tangential line at the first contact point;

a second tangential line at the second contact point;

a first point where the first tangential line and an extension line of the first lower side meet;

a second point where the second tangential line and an extension line of the second lower side meet;

a first segment connecting the first and second points to each other;

a third point where the first tangential line and the second tangential line meet;

a fourth point where an extension line of the first lower side and an extension line of the second lower side meet;

a second segment connecting the third and fourth points to each other; and

a fifth point where the first segment and the second segment intersect, the fifth point being higher than a center of the second segment.

6. The semiconductor device as claimed in claim 5, wherein a first distance from the third point to the fifth point is about 0.2 times to about 0.45 times a length of the second segment.

7. The semiconductor device as claimed in any one of claims 1 to 6, ~~further comprising:~~

~~a second active fin protruding from the substrate;~~

~~a second gate pattern covering a side surface and a top surface of the second active fin; and~~

~~second source/drain patterns at opposite sides of the second gate pattern, the second source/drain pattern including:~~

~~a third lower side and a fourth lower side spaced apart from each other,~~

~~a third upper side extended from a top end of the third lower side, and~~

~~a fourth upper side extended from the fourth lower side,~~

wherein a width of the second source/drain pattern is larger than a width of the first source/drain pattern.

~~8. The semiconductor device as claimed in claim 7, wherein the third lower side is inclined at a third angle relative to a straight line connecting a bottom end of the third lower side to a bottom end of the fourth lower side, the first angle being greater than the third angle.~~

~~9~~8. The semiconductor device as claimed in claim 7, wherein the fourth upper side is inclined at a ~~third~~ fourth angle relative to the ~~second segment~~top surface of the substrate, the ~~second~~ fourth angle being substantially equal to the third angle.

~~10. The semiconductor device as claimed in any one of claims 7 to 9, wherein the first source/drain pattern and the first gate pattern constitute an NMOS transistor, and the second source/drain pattern and the second gate pattern constitute a PMOS transistor.~~

~~11~~9. The semiconductor device as claimed in any one of claims 1 to 6, ~~further comprising:~~

~~a second active fin protruding from the substrate,~~ wherein the second active fin being spaced apart from the first active fin;

~~a second gate pattern crossing the second active fin;~~

~~second source/drain patterns on the second active fin and at opposite sides of the second gate pattern,~~ the second source/drain pattern~~s~~ having a same shape as the first source/drain pattern~~s, and~~;

the second source/drain pattern~~s~~ having a different size from that of the first source/drain pattern~~s; and~~

~~a spacer below each of the second source/drain patterns to cover a side surface of the second active fin~~.

~~12~~10. The semiconductor device as claimed in claim ~~11~~9~~, wherein each of the second source/drain patterns includes:~~

~~a third lower side and a fourth lower side spaced apart from each other;~~

~~a third upper side extended from a top end of the third lower side; and~~

~~a fourth upper side extended from the fourth lower side,~~

wherein a width of the second source/drain pattern is smaller than a width of the first source/drain pattern, and

a height of a top end~~s~~ of the first source/drain pattern~~s~~ is substantially equal to a height of a top end~~s~~ of the second source/drain pattern~~s~~.

~~13~~11. The semiconductor device as claimed in claim ~~11~~9~~, wherein each of the second source/drain patterns includes:~~

~~a third lower side and a fourth lower side spaced apart from each other;~~

~~a third upper side extended from a top end of the third lower side; and~~

~~a fourth upper side extended from the fourth lower side,~~

~~wherein the third lower side is inclined at a third angle relative to a straight line connecting a bottom end of the third lower side to a bottom end of the fourth lower side,~~

wherein the fourth upper side is inclined at a fourth angle relative to a ~~second~~ third segment connecting a third point, where the third lower side and the third upper side meet, with a fourth point where the fourth lower side and the fourth upper side meet, and

wherein the third angle is greater than the fourth angle.

~~14~~12. A semiconductor device, comprising:

a substrate including a first region and a second region;

a first active fin protruding from the substrate, on the first region;

a first source/drain pattern of a first conductivity on the first active fin;

a second active fin protruding from the substrate, on the second region; ~~and~~

a second source/drain pattern of a second conductivity on the second active fin, the second conductivity being opposite to the first conductivity, a largest width of the first source/drain pattern in a first direction being different from a largest width of the second source/drain pattern in the first direction;

a first gate pattern crossing over both the first active fin and the second active fin; and

a contact plug in direct contact with both the first source/drain pattern of the first conductivity and the second source/drain pattern of the second conductivity, an entire bottom surface of the contact plug being flat,

wherein the first source/drain pattern includes:

a first lower side and a second lower side spaced apart from each other;

a first upper side extended from a top end of the first lower side; and

a second upper side extended from the second lower side,

wherein the second source/drain pattern includes:

a third lower side and a fourth lower side spaced apart from each other;

a third upper side extended from a top end of the third lower side; and

a fourth upper side extended from the fourth lower side,

wherein the first lower side is inclined at a first angle relative to a straight line connecting a bottom end of the first lower side to a bottom end of the second lower side,

wherein the second upper side is inclined at a second angle relative to a first segment connecting a first point, where the first lower side and the first upper side meet, with a second point, where the second lower side and the second upper side meet,

wherein the third lower side is inclined at a third angle relative to a straight line connecting a bottom end of the third lower side to a bottom end of the fourth lower side, and wherein the first angle is greater than the second angle and the third angle,

wherein top surfaces of the first and second source/drain patterns are coplanar with each other, the top surfaces of the first and second source/drain patterns being in direct contact with the bottom surface of the contact plug.

~~15. The semiconductor device as claimed in claim 14, wherein the first source/drain pattern includes:~~

~~a first lower side and a second lower side spaced apart from each other;~~

~~a first upper side extended from a top end of the first lower side; and~~

~~a second upper side extended from the second lower side,~~

~~wherein the first lower side is inclined at a first angle relative to a straight line connecting a bottom end of the first lower side to a bottom end of the second lower side,~~

~~wherein the second upper side is inclined at a second angle relative to a first segment connecting a first point, where the first lower side and the first upper side meet, with a second point, where the second lower side and the second upper side meet, and~~

~~wherein the first angle is greater than the second angle.~~

~~16~~13. The semiconductor device as claimed in claim ~~15~~12, further comprising:

a third point where the first upper side and the second upper side meet;

a fourth point where an extension line of the first lower side and an extension line of the second lower side meet;

a second segment connecting the third point to the fourth point; and

a fifth point where the first segment and the second segment intersect, the fifth point being higher than a center point of the second segment.

~~17. The semiconductor device as claimed in claim 15 or claim 16, wherein the second source/drain pattern includes:~~

~~a third lower side and a fourth lower side spaced apart from each other;~~

~~a third upper side extended from a top end of the third lower side; and~~

~~a fourth upper side extended from the fourth lower side,~~

~~wherein the third lower side is inclined at a third angle relative to a straight line connecting a bottom end of the third lower side to a bottom end of the fourth lower side, and the first angle is greater than the third angle.~~

~~18~~14. A semiconductor device, comprising:

a substrate including a first region and a second region;

a first active fin protruding from the substrate, on the first region;

a first source/drain pattern of a first conductivity on the first active fin;

a second active fin protruding from the substrate, on the second region; ~~and~~

a second source/drain pattern of a second conductivity on the second active fin, the second conductivity being opposite to the first conductivity, the first source/drain pattern having a same shape as the second source/drain pattern, and a size of the first source/drain pattern being different from that of the second source/drain pattern;

a first gate pattern crossing over both the first active fin and the second active fin; and

a contact plug in direct contact with both the first source/drain pattern of the first conductivity and the second source/drain pattern of the second conductivity, an entire bottom surface of the contact plug being flat,

wherein the first source/drain pattern includes:

a first lower side and a second lower side spaced apart from each other;

a first upper side extended from a top end of the first lower side; and

a second upper side extended from the second lower side,

wherein the second source/drain pattern includes:

a third lower side and a fourth lower side spaced apart from each other;

a third upper side extended from a top end of the third lower side; and

a fourth upper side extended from the fourth lower side,

wherein the first lower side is inclined at a first angle relative to a straight line connecting a bottom end of the first lower side with a bottom end of the second lower side,

wherein the second upper side is inclined at a second angle relative to a first segment connecting a first point where the first lower side and the first upper side meet with a second point where the second lower side and the second upper side meet,

wherein the third lower side is inclined at a third angle relative to a straight line connecting a bottom end of the third lower side to a bottom end of the fourth lower side, the first angle being greater than the second angle and the third angle,

wherein top surfaces of the first and second source/drain patterns are coplanar with each other, the top surfaces of the first and second source/drain patterns being in direct contact with the bottom surface of the contact plug.

~~19. The semiconductor device as claimed in claim 18, wherein the first source/drain pattern includes:~~

~~a first lower side and a second lower side spaced apart from each other;~~

~~a first upper side extended from a top end of the first lower side; and~~

~~a second upper side extended from the second lower side,~~

~~wherein the first lower side is inclined at a first angle relative to a straight line connecting a bottom end of the first lower side with a bottom end of the second lower side, and~~

~~wherein the second upper side is inclined at a second angle relative to a first segment connecting a first point where the first lower side and the first upper side meet with a second point where the second lower side and the second upper side meet, the first angle being greater than the second angle.~~

~~20~~15. The semiconductor device as claimed in claim ~~18 or claim 19~~14, further comprising a spacer below the second source/drain pattern to cover a side surface of the second active fin.